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Team Nexperia



# PMEG2005EPK

# 20 V, 0.5 A low VF MEGA Schottky barrier rectifier Rev. 2 — 14 March 2012

Product data sheet

## **Product profile**

## 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

#### 1.2 Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 0.5 A
- Reverse voltage: V<sub>R</sub> ≤ 20 V
- Low forward voltage V<sub>F</sub> ≤ 410 mV
- Low reverse current

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	square wave; $\bar{\delta}$ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 130 °C	<u>[1]</u>	-	-	0.5	Α
		square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 140 °C		-	-	0.5	А
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>F</sub>	forward voltage	$I_F$ = 500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C		-	360	410	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C		-	30	130	μA
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$		-	3	-	ns

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		. 54 .
2	A	anode	1 2	1 <del>]   2</del> sym001
			Transparent top view	
			SOD1608 (DFN1608D-2	2)

<sup>[1]</sup> The marking bar indicates the cathode.

## 3. Ordering information

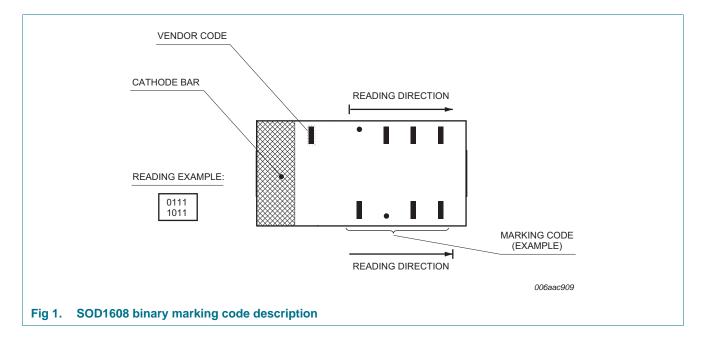
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG2005EPK	DFN1608D-2	Leadless ultra small plastic package; 2 terminals	SOD1608			

## 4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2005EPK	1000 0000



## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		· · · · · · · · · · · · · · · · · · ·				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C		-	20	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 135 °C		-	0.7	Α
I <sub>F(AV)</sub>	average forward current	square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>amb</sub> ≤ 130 °C	<u>[1]</u>	-	0.5	А
		square wave; $\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 140 °C		-	0.5	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.5$		-	2	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$		-	3	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	390	mW
			[3]	-	830	mW
			[1]	-	1470	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1][2]	-	-	320	K/W
	from junction to ambient		[1][3]	-	-	150	K/W
	ambient		[1][4]	-	-	85	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[5]</u>	-	-	20	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

<sup>[5]</sup> Soldering point of cathode tab.

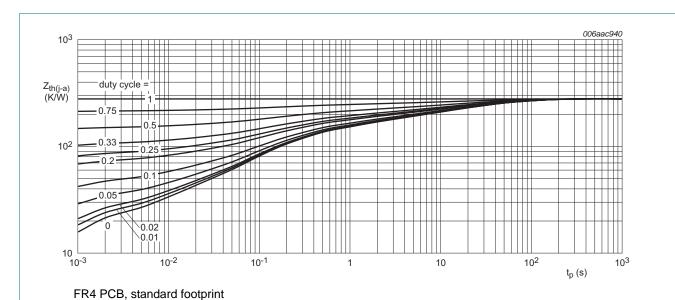


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

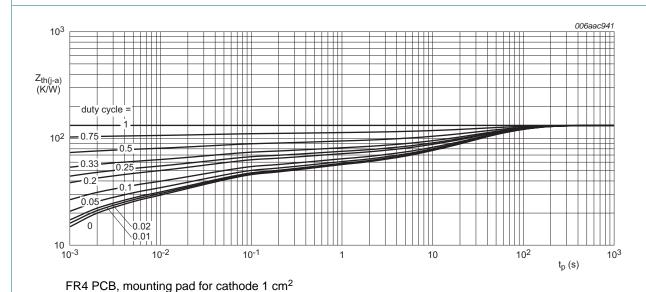
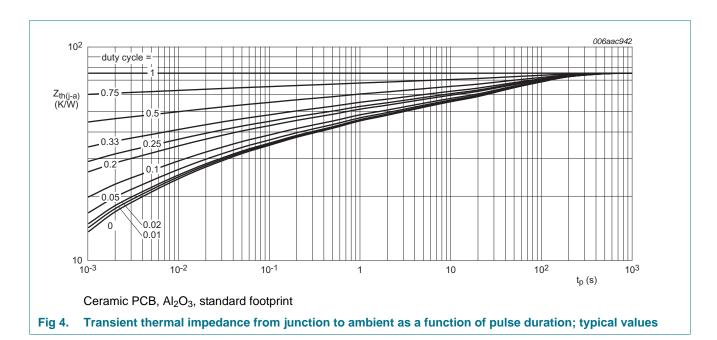


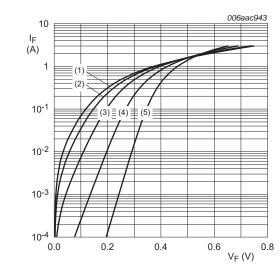
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	270	300	mV
		$I_F$ = 500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	360	410	mV
I <sub>R</sub> reverse current	$V_R = 10 \text{ V}; T_j = 25 \text{ °C}$	-	30	130	μΑ	
		V <sub>R</sub> = 20 V; T <sub>j</sub> = 25 °C	-	70	300	μΑ
C <sub>d</sub> diode	diode capacitance	$V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	35	-	pF
		$V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	13	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	3	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ mA/}\mu\text{s}; T_j = 25 \text{ °C}$	-	380	-	mV



- (1)  $T_i = 150 \, ^{\circ}C$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \, ^{\circ}C$
- (4) T<sub>j</sub> = 25 °C
- (5) T<sub>i</sub> = −40 °C

Fig 5. Forward current as a function of forward voltage; typical values

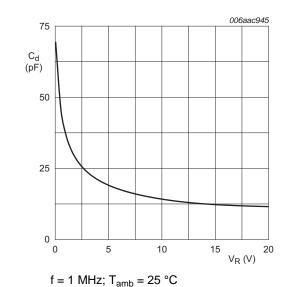
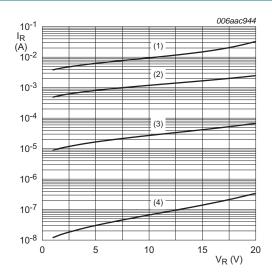
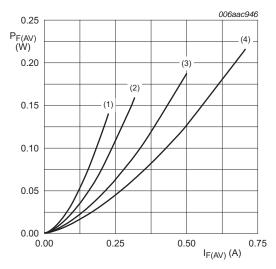


Fig 7. Diode capacitance as a function of reverse voltage; typical values



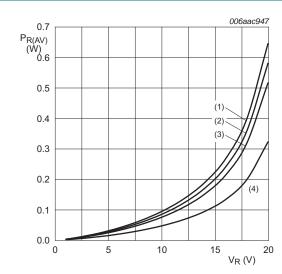
- (1)  $T_j = 125 \, ^{\circ}C$
- (2)  $T_i = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, ^{\circ}C$
- (4)  $T_i = -40 \, ^{\circ}\text{C}$

Fig 6. Reverse current as a function of reverse voltage; typical values



- T<sub>i</sub> = 150 °C
- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 125 °C

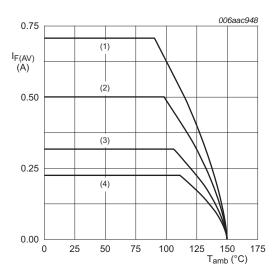
(1)  $\delta = 1$ 

(2)  $\delta = 0.9$ 

(3)  $\delta = 0.8$ 

(4)  $\delta = 0.5$ 

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

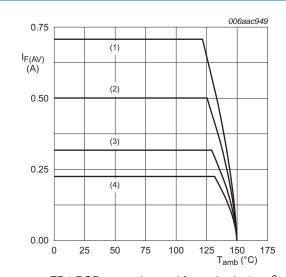
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1  $\mbox{cm}^2$ 

T<sub>i</sub> = 150 °C

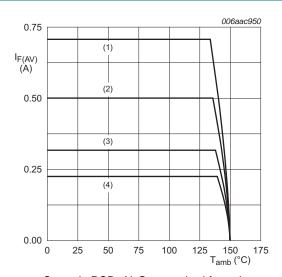
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

 $T_i = 150 \, ^{\circ}C$ 

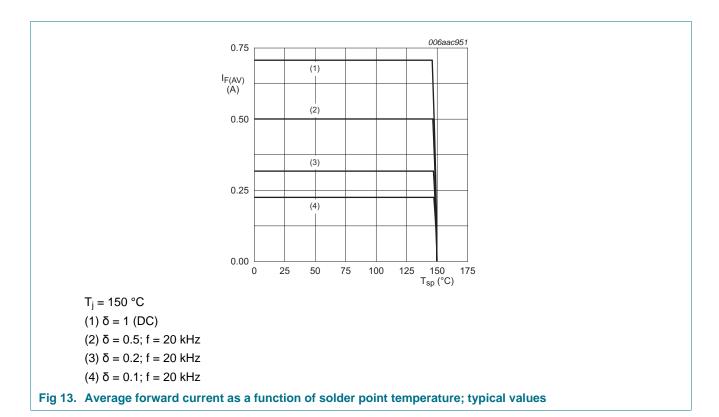
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

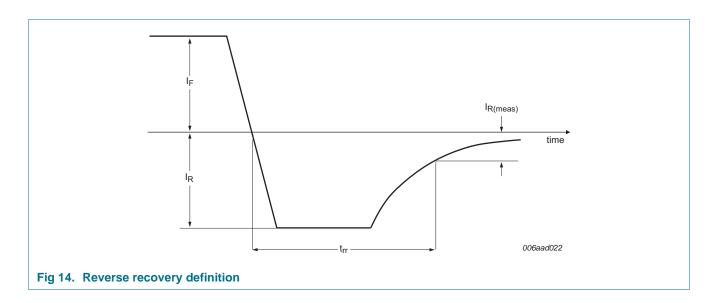
(3)  $\delta = 0.2$ ; f = 20 kHz

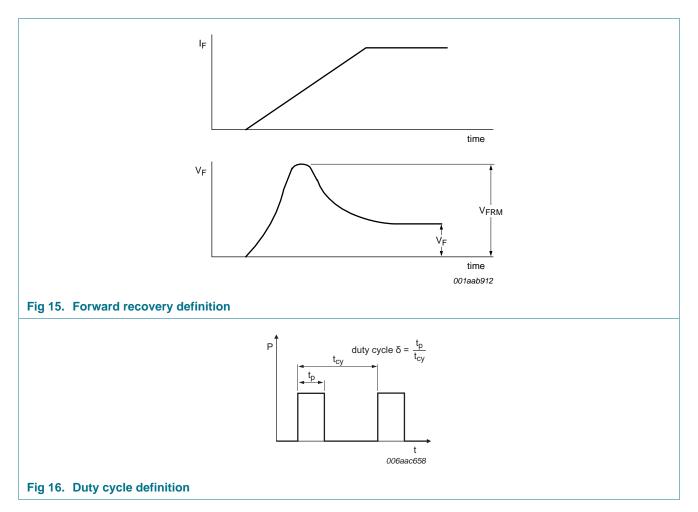
(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of ambient temperature; typical values



## 8. Test information



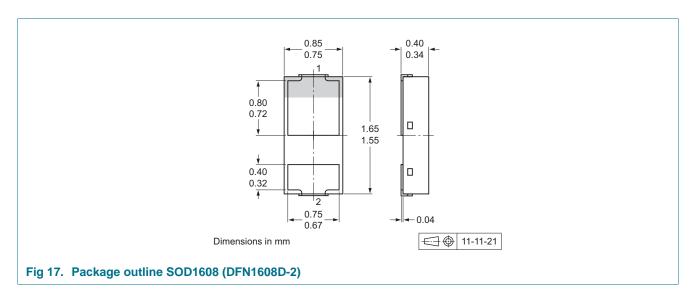


The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

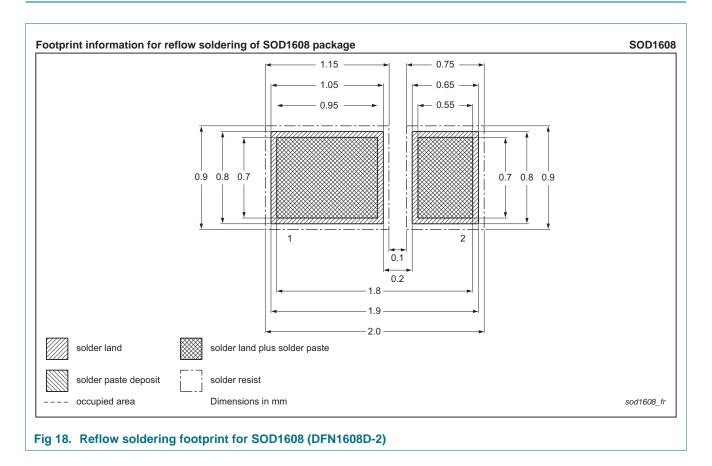
## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Soldering





## 11. Revision history

#### Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2005EPK v.2	20120314	Product data sheet	-	PMEG2005EPK v.1
Modifications:		lues": I <sub>F</sub> corrected stics": t <sub>rr</sub> and V <sub>FRM</sub> added 5: added		
PMEG2005EPK v.1	20120112	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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PMEG2005EPK

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## PMEG2005EPK

## 20 V, 0.5 A low VF MEGA Schottky barrier rectifier

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# PMEG2005EPK

## 20 V, 0.5 A low VF MEGA Schottky barrier rectifier

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